

IN THE CLAIMS:

Please amend the claims as follows:

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3. (Amended) A method according to claim 1, whereby the measuring is made after processing steps, such as development, etching, blasting or high-temperature processing, following the exposure.

4. (Amended) A method according to claim 1, whereby the first and the second mask are based on the same input data.

5. (Amended) A method according to claim 1, whereby the first mask is a reference mask based on reference input data, whereas the second mask is based on the actual product data.

6. (Amended) A method according to claim 1, whereby the compensation used is a statistical mean value of the compensation according to the measurement and compensation according to prior measurements.

7. (Amended) A method according to claim 1, wherein at least one additional measurement is made during the process, whereby the compensations is a statistical mean value of compensation parts related to the process before the first measurement, and the process between the measurements.

8. (Amended) A method according to claim 1, whereby the thickness of the sensitive layer before the exposure on the mask blank or on the substrate is measured, whereby said measurement data are used for additional compensation.

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COK*

9. (Amended) A method according to claim 1, whereby already existing patterns on the substrate is measured prior to the exposure, whereby said measurement is used for additional compensation.

10. (Amended) A method according to claim 1, whereby said method is performed once for each substrate batch used in said fabrication.

11. (Amended) A method according to claim 1, whereby the measurement comprises measurement of position errors and pattern line width errors.

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12. (Amended) A method according to claim 1, whereby said compensation is performed by time offsets or room offsets in the pattern writer used for producing the second mask.

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15. (Amended) A system according to claim 13, comprising at least one additional measuring device, whereby the compensations is a statistical mean value of compensation parts related to the process before the first measurement, and the process between the measurements.

16. (Amended) A system according to claim 13, whereby the first and the second mask generator (1) are the same device.

17. (Amended) A system accoding to claim 13, further comprising a second measuring device (4) for measuring the thickness of the light sensitive layer on the substrate prior to the exposure, whereby said measurement is used for additional compensation.

18. (Amended) A system according to claim 13, further comprising a third measuring device (4) for measuring of existing

patterns on the substrate prior to the exposure, whereby said measurement is used for additional compensation.

*HB COTX*

19. (Amended) A system according to claim 13, whereby the first measuring device comprises means for measurement of position errors and pattern line width errors.

20. (Amended) A system according to claim 13, Whereby said mask generator comprises a pattern writer, being controllable for said compensations by means of time offsets during the writing.

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TECHNICAL DRAWING AND SPECIFICATIONS